



**Modul / Module**

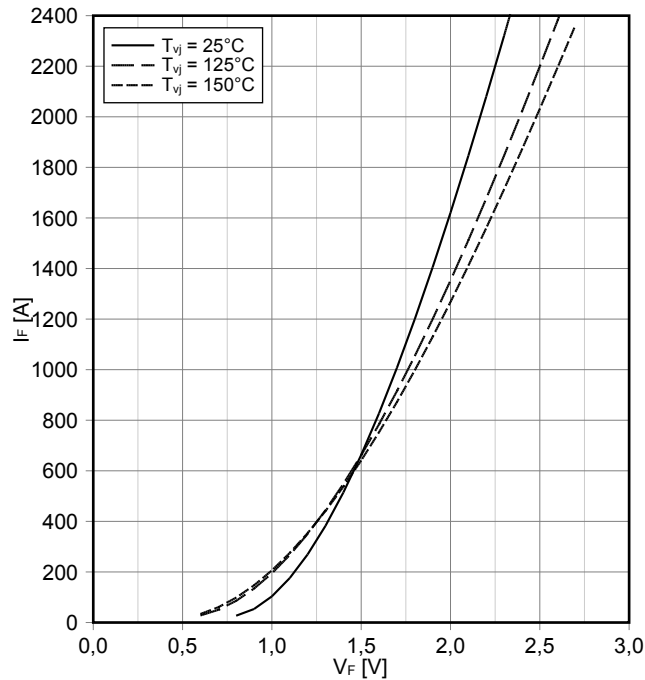
Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	4,0		kV
Material Modulgrundplatte Material of module baseplate			AlSiC		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		32,2 32,2		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		19,1 19,1		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 400		
			min.	typ.	max.
Modulstreuinduktivität Stray inductance module		L <sub>SCE</sub>		18	nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T <sub>c</sub> = 25°C, pro Schalter / per switch	R <sub>AA'+CC'</sub>		0,24	mΩ
Lagertemperatur Storage temperature		T <sub>stg</sub>	-40		150 °C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M6 - Montage gem. gültiger Applikationsschrift Screw M6 - Mounting according to valid application note	M	4,25		5,75 Nm
Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque	Schraube M4 - Montage gem. gültiger Applikationsschrift Screw M4 - Mounting according to valid application note	M	1,8	-	2,1 Nm
	Schraube M8 - Montage gem. gültiger Applikationsschrift Screw M8 - Mounting according to valid application note		8,0	-	10 Nm
Gewicht Weight		G		800	g

Dynamische Daten gehen in Verbindung mit FD1200R17HP4-K\_B2 Modul  
Dynamic data valid in conjunction with FD1200R17HP4-K\_B2 module

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**Durchlasskennlinie der Diode, Wechselrichter (typisch)**  
forward characteristic of Diode, Inverter (typical)

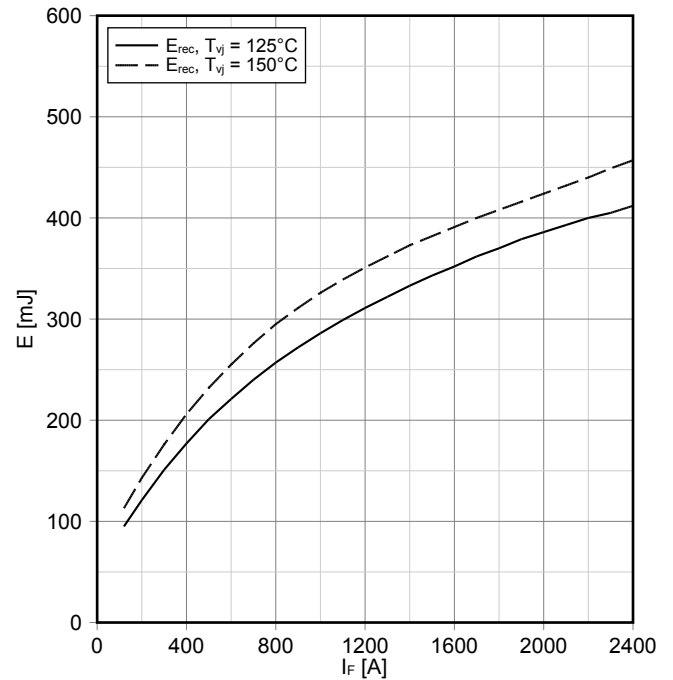
$I_F = f(V_F)$



**Schaltverluste Diode, Wechselrichter (typisch)**  
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$

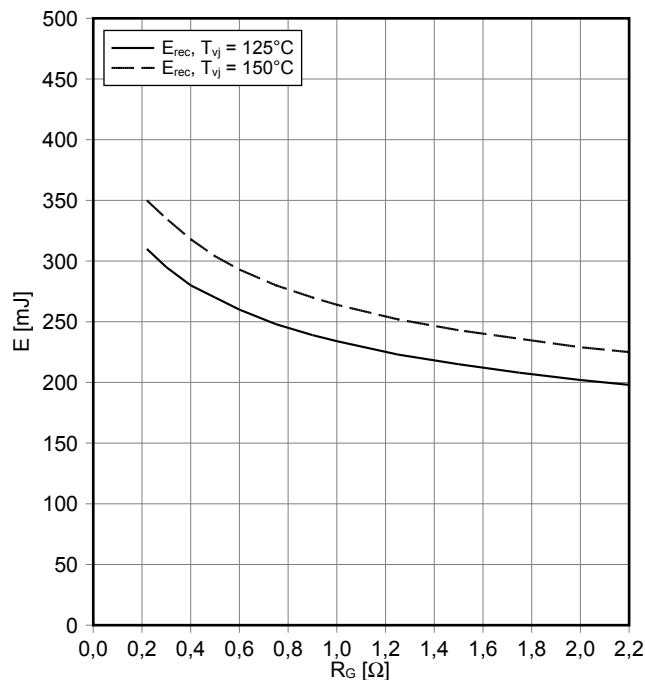
$R_{Gon} = \Omega, V_{CE} = 900\text{ V}$



**Schaltverluste Diode, Wechselrichter (typisch)**  
switching losses Diode, Inverter (typical)

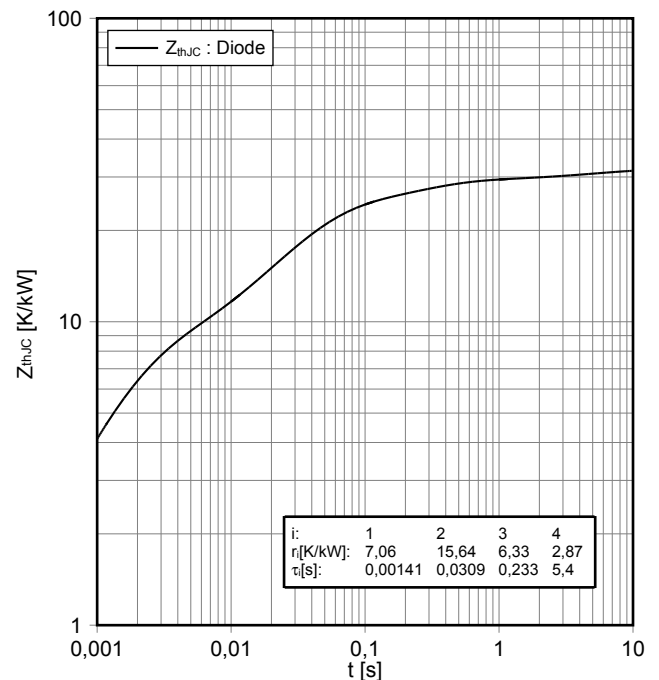
$E_{rec} = f(R_G)$

$I_F = 1200\text{ A}, V_{CE} = 900\text{ V}$



**Transienter Wärmewiderstand Diode, Wechselrichter**  
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$



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